

IXYS

CS 60

Phase Control Thyristor

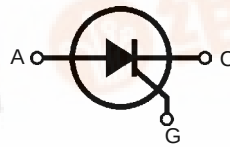
$$V_{RRM} = 1200-1600 \text{ V}$$

$$I_{T(RMS)} = 75 \text{ A}$$

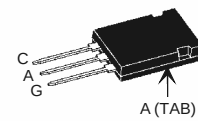
$$I_{T(AV)M} = 48 \text{ A}$$

Preliminary Data Sheet

V_{RSM}	V_{RRM}	Type
V_{DSM}	V_{DRM}	
V	V	
1300	1200	CS 60-12io1
1500	1400	CS 60-14io1
1700	1600	CS 60-16io1



PLUS247



C = Cathode, A = Anode, G = Gate

Symbol	Test Conditions	Maximum Ratings
$I_{T(RMS)}$	$T_{VJ} = T_{VJM}$ (lead current limit)	75 A
$I_{T(AV)M}$	$T_C = 105^\circ\text{C}$; 180° sine	48 A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0 \text{ V}$	t = 10 ms (50 Hz), sine 1500 A t = 8.3 ms (60 Hz), sine 1600 A
	$T_{VJ} = T_{VJM}$; $V_R = 0 \text{ V}$	t = 10 ms (50 Hz), sine 1350 A t = 8.3 ms (60 Hz), sine 1450 A
i^2t	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0 \text{ V}$	t = 10 ms (50 Hz), sine 11,200 A ² s t = 8.3 ms (60 Hz), sine 10,750 A ² s
	$T_{VJ} = T_{VJM}$; $V_R = 0 \text{ V}$	t = 10 ms (50 Hz), sine 9100 A ² s t = 8.3 ms (60 Hz), sine 8830 A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$; f = 50 Hz; $t_p = 200 \mu\text{s}$; $V_D = 2/3 V_{DRM}$; $I_G = 0.3 \text{ A}$; $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	repetitive, $I_T = 60 \text{ A}$ 150 A/ μs
		non repetitive, $I_T = I_{T(AV)M}$ 500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$ 1000 V/ μs
P_{GM}	$T_{VJ} = T_{VJM}$; $I_T = I_{T(AV)M}$	$t_p = 30 \mu\text{s}$ 10 W $t_p = 300 \mu\text{s}$ 5 W
$P_{G(AV)}$		0.5 W
V_{RGM}		10 V
T_{VJ}		-40...+140 °C
T_{VJM}		140 °C
T_{stg}		-40...+125 °C
F_C	Mounting Force	20...120/4.5...27 N/lbs
Weight		6 g

Features

- Thyristor for line frequency
- International standard package JEDEC TO-247
- Planar passivated chip
- Long-term stability of blocking currents and voltages

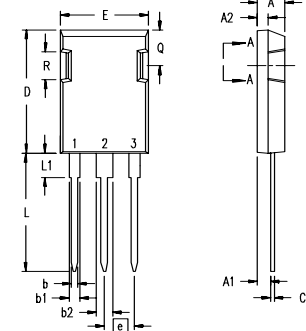
Applications

- Motor control
- Power converter
- AC power controller
- Switch-mode and resonant mode power supplies
- Light and temperature control

Advantages

- Easy to mount
- Space and weight savings
- Simple mounting

Symbol	Test Conditions	Characteristic Values
I_R, I_D	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$ $T_{VJ} = 25^\circ\text{C}$	$\leq 10 \text{ mA}$ $\leq 0.2 \text{ mA}$
V_T	$I_T = 100 \text{ A}; T_{VJ} = 25^\circ\text{C}$	$\leq 1.4 \text{ V}$
V_{T0}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.85 V
r_T		$3.7 \text{ m}\Omega$
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	$\leq 1.5 \text{ V}$ $\leq 1.6 \text{ V}$
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	$\leq 100 \text{ mA}$ $\leq 200 \text{ mA}$
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	$\leq 0.2 \text{ V}$
I_{GD}		$\leq 10 \text{ mA}$
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	$\leq 450 \text{ mA}$
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	$\leq 200 \text{ mA}$
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	$\leq 2 \mu\text{s}$
R_{thJC}	DC current	0.32 K/W
R_{thJK}	DC current	0.47 K/W

PLUS247™ Outline


Terminals: 1 - Cathode
2 - Anode
3 - Gate
Tab - Anode

Dim.	Millimeter	Inches
	Min. Max.	Min. Max.
A	4.83 5.21	.190 .205
A ₁	2.29 2.54	.090 .100
A ₂	1.91 2.16	.075 .085
b	1.14 1.40	.045 .055
b ₁	1.91 2.13	.075 .084
b ₂	2.92 3.12	.115 .123
C	0.61 0.80	.024 .031
D	20.80 21.34	.819 .840
E	15.75 16.13	.620 .635
e	5.45 BSC	.215 BSC
L	19.81 20.32	.780 .800
L1	3.81 4.32	.150 .170
Q	5.59 6.20	.220 0.244
R	4.32 4.83	.170 .190

Leads and tab are solder plated.